

# KM91028NF

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| 1. Material                                    | GaAlAs                                       |
| 2. Electrode                                   | N (cathode) side : Au<br>P (anode) side : Au |
| 3. Electrode pattern                           | Fig.1  |
| 4. Chip size                                   | 0.265 mm × 0.265 mm × 0.175 mm (Fig.1)       |
| 5. Emission area                               | 0.230mm X 0.230mm (Fig.1)                    |
| 6. Electro-Optical characteristics (Ta = 25°C) |  |

Parameters	Symbol	Condition	Min	Typ	Max	Unit
Power	Po	IF=20mA	1.6	3.8	-	mW
Forward Voltage	VF	IF=20mA	-	1.37	1.41	V
Reverse Current	IR	VR=3V	-	-	10	uA
Peak Wavelength	$\lambda_p$	IF=20mA	900	910	915	nm
Spectral Radiation Bandwidth	$\Delta\lambda(*)$	IF=20mA	-	45	-	nm

\* (\*) mark is reference data

\* Power Measurement at Resonac Photonics.

7. Recommended bonding method    Ultra-sonic method or a combination of ultra-sonic and thermo-compression methods.

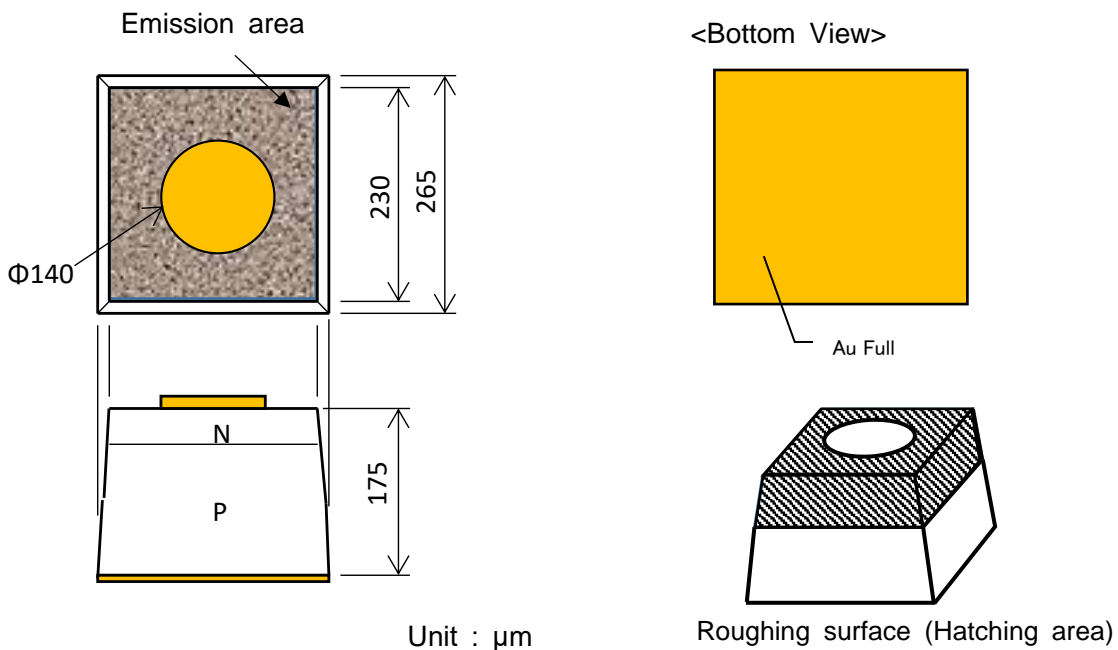


Fig.1 : Chip size and Emission area and Electrode pattern

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